NCE N-Channel Enhancement Mode Power MOSFET

Description

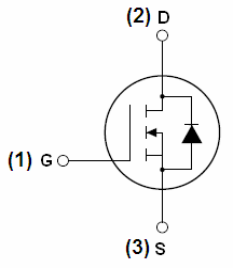
The NCE80H16WD uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} =80V,I_D =160A
  $R_{DS(ON)}$ <4.5mΩ @ V_{GS}=10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Automotive applications
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram

TO-263T-2L top view

100% UIS TESTED!

100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE80H16WD	NCE80H16WD	TO-263T-2L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	160	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	113	A
Pulsed Drain Current	I_{DM}	500	A
Maximum Power Dissipation	P_D	285	W
Derating factor		1.9	W/℃
Single pulse avalanche energy (Note 5)	E_{AS}	1936	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristics

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	0.53	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

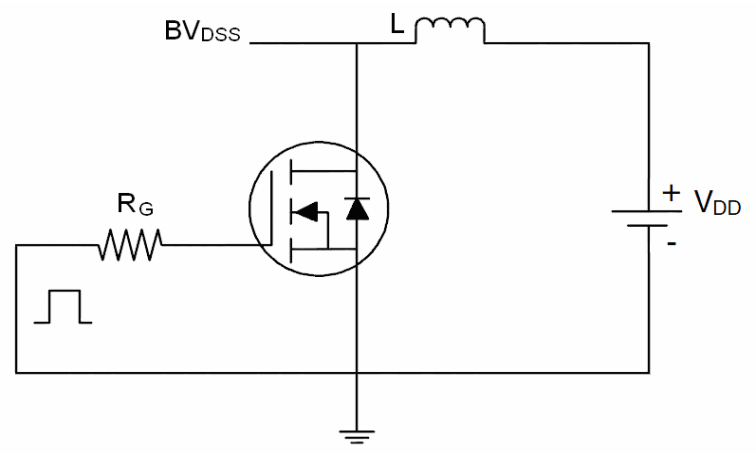
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	80	88	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	2	3	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A	-	3.5	4.5	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=20A	60	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=25V,V_{GS}=0V, F=1.0MHz	-	6500	-	PF
Output Capacitance	C_{oss}		-	810	-	PF
Reverse Transfer Capacitance	C_{rss}		-	310	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=40V,R_L=15Ω V_{GS}=10V,R_G=2.5Ω	-	31.5	-	nS
Turn-on Rise Time	t_r		-	33	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	46	-	nS
Turn-Off Fall Time	t_f		-	17.5	-	nS
Total Gate Charge	Q_g	V_{DS}=40V,I_D=20A, V_{GS}=10V	-	130		nC
Gate-Source Charge	Q_{gs}		-	36		nC
Gate-Drain Charge	Q_{gd}		-	46		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=40A	-		1.2	V
Diode Forward Current (Note 2)	I_S		-	-	160	A
Reverse Recovery Time	t_{rr}	TJ = 25°C, IF = 20A di/dt = 500A/μs (Note3)	-	51	-	nS
Reverse Recovery Charge	Qrr		-	61	-	nC

Notes:

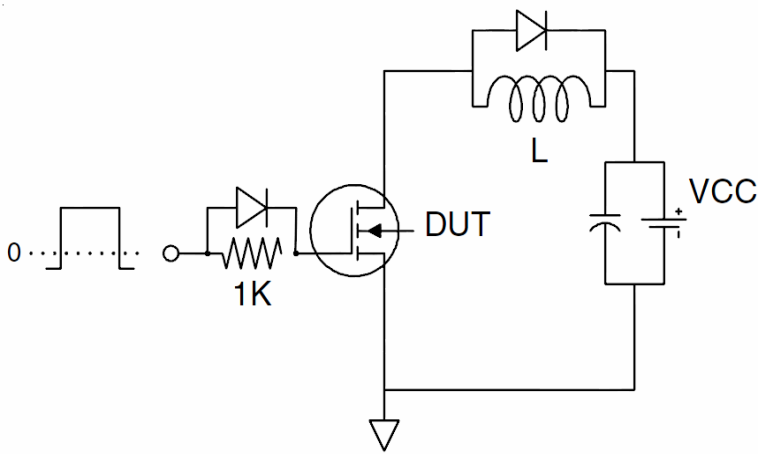
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition：Tj=25℃,V_{DD}=40V,V_G=10V,L=0.5mH,Rg=25Ω

Test circuit

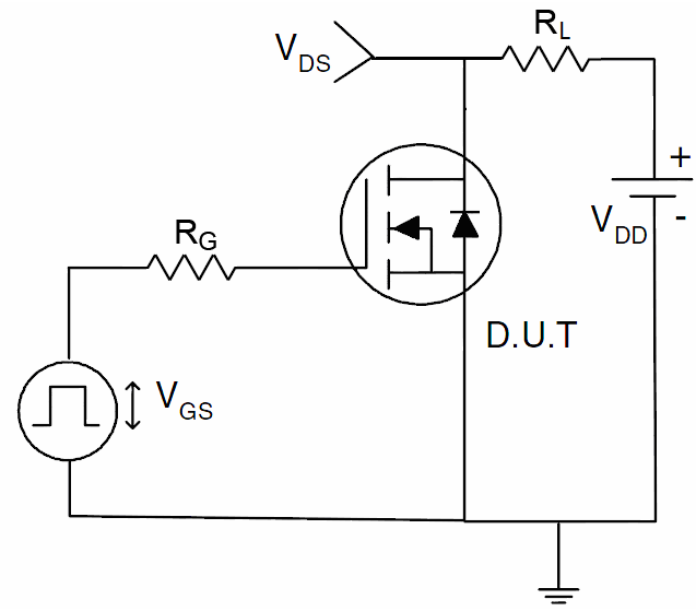
1）E_{AS} test Circuit



2）Gate charge test Circuit



3）Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

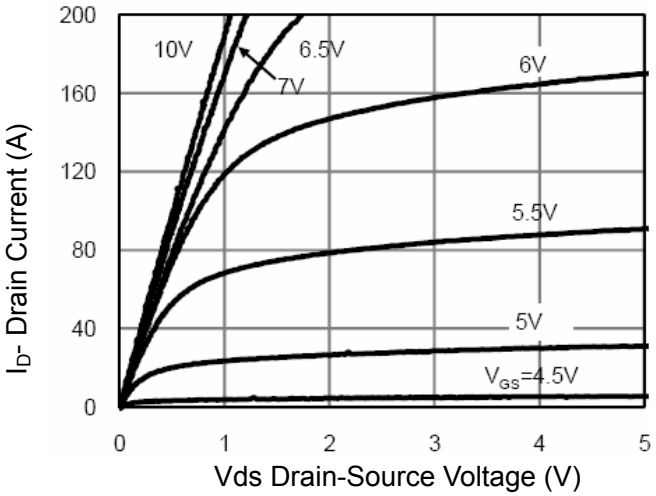


Figure 1 Output Characteristics

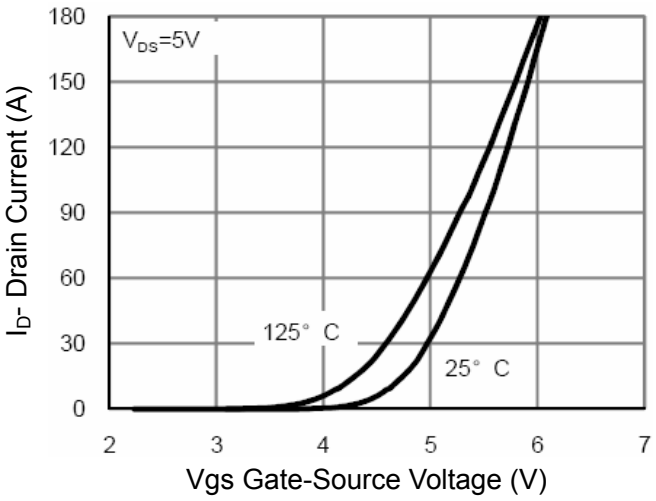


Figure 2 Transfer Characteristics

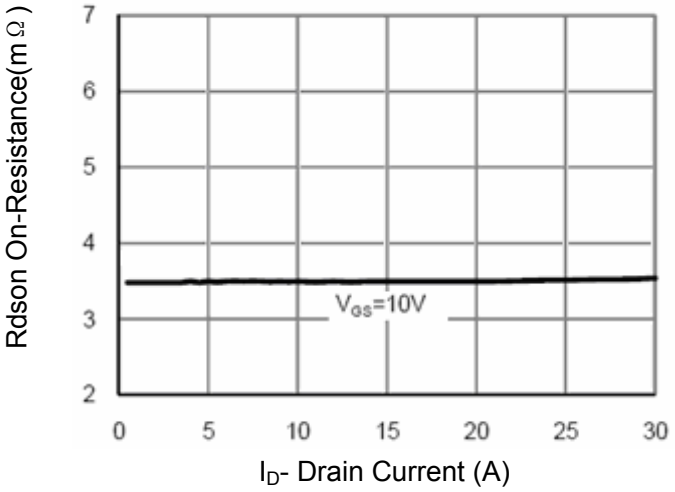


Figure 3 Rdson- Drain Current

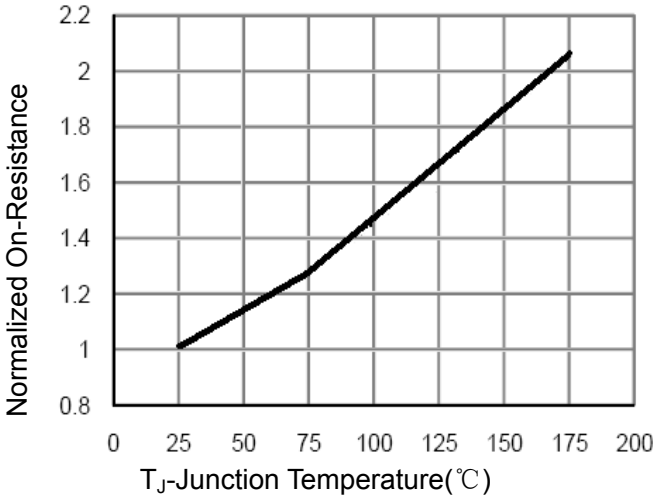


Figure 4 Rdson-JunctionTemperature

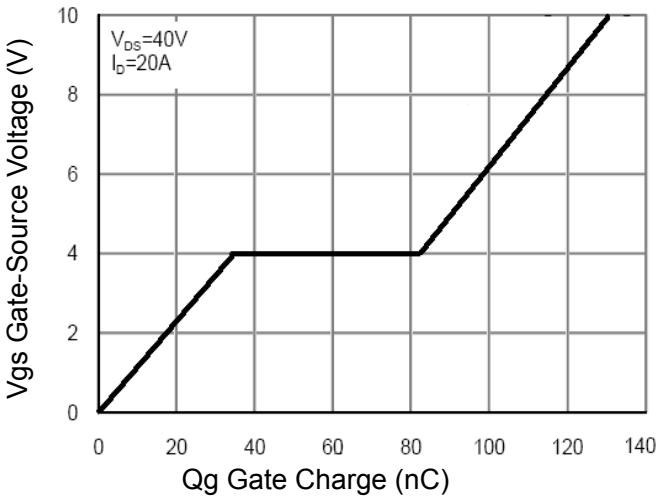


Figure 5 Gate Charge

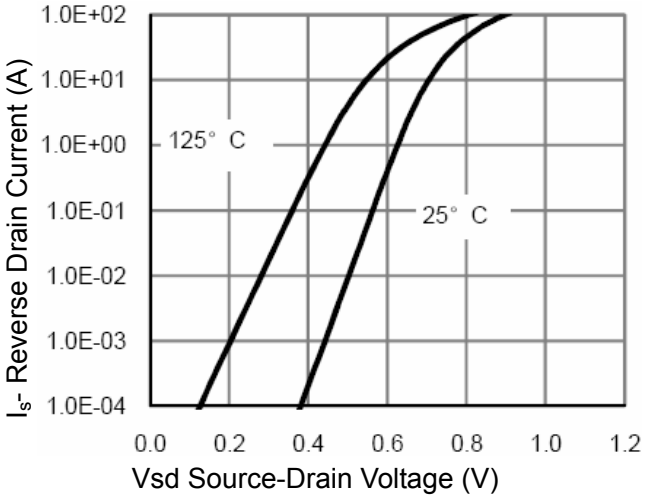


Figure 6 Source- Drain Diode Forward

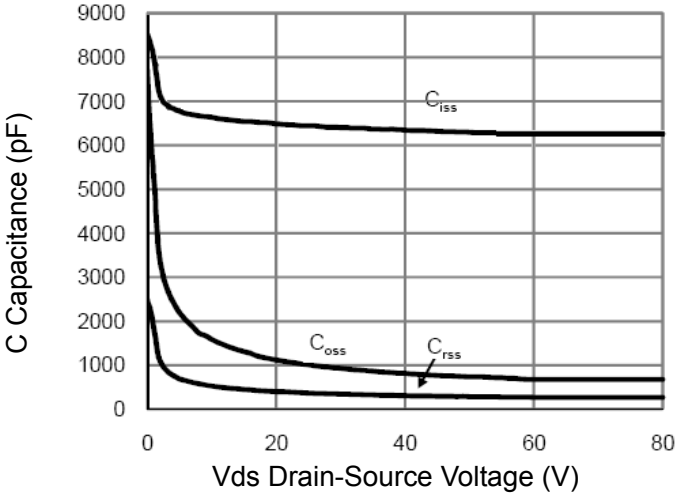


Figure 7 Capacitance vs Vds

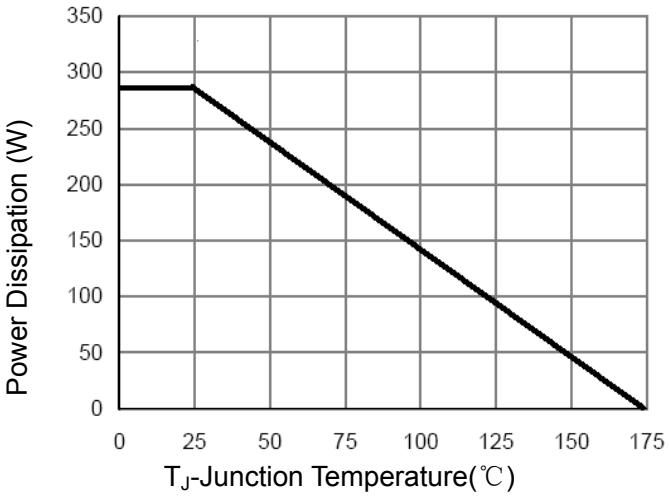


Figure 9 Power De-rating

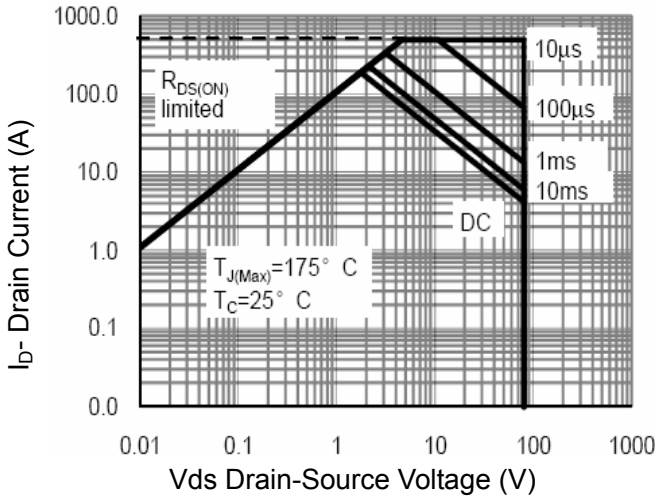


Figure 8 Safe Operation Area

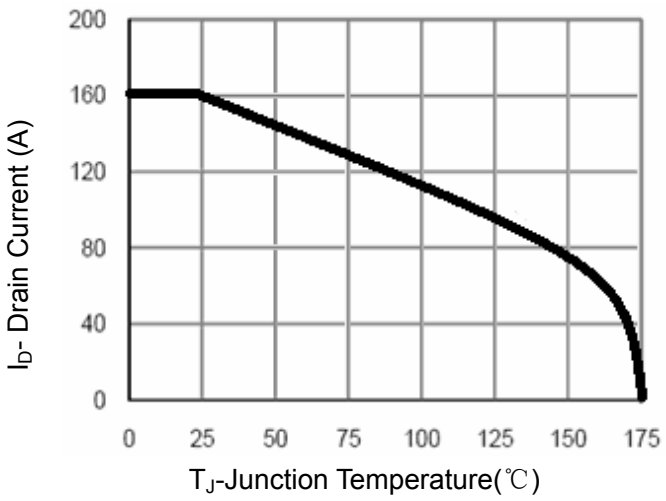


Figure 10 Current De-rating

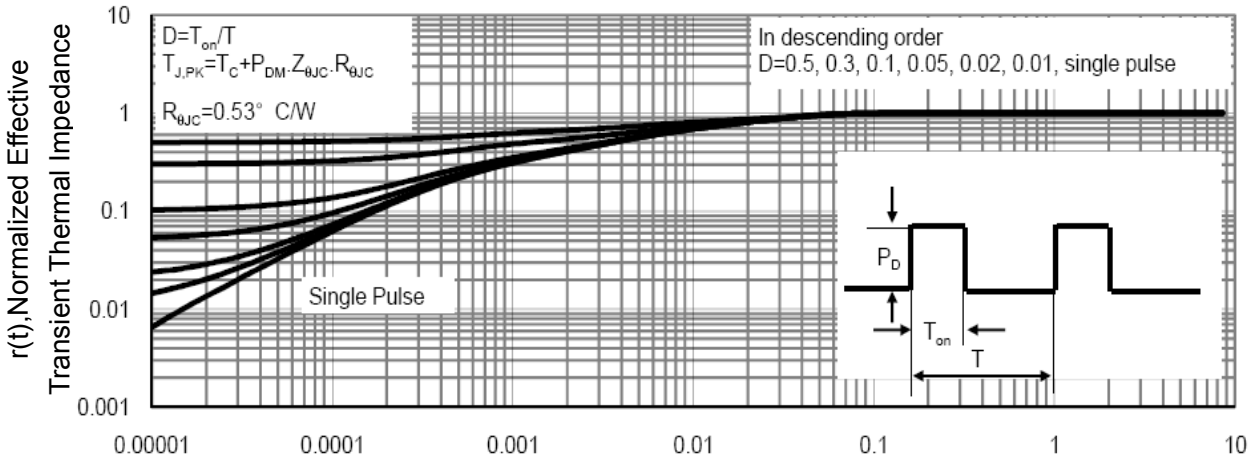
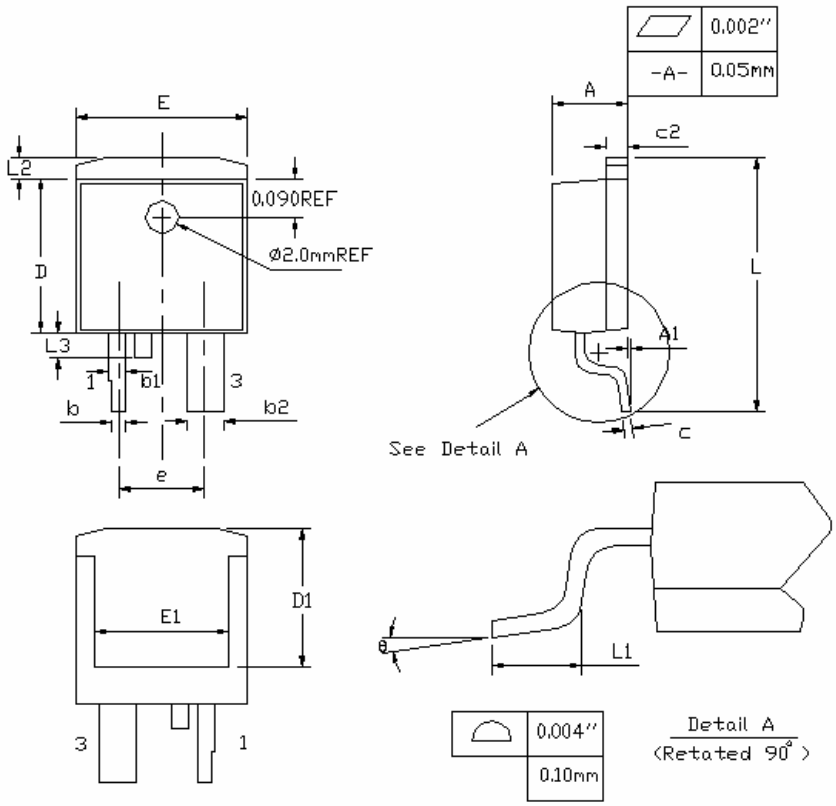


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263T-2L Package Information



SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.170	0.180	4.32	4.57	
A1	-	0.010	-	0.25	
b	0.028	0.037	0.71	0.94	
b 1	0.035	0.047	0.9	1.2	
b2	0.081	0.095	2.05	2.4	
c	0.018	0.024	0.46	0.61	
c2	0.048	0.055	1.22	1.40	
D	0.350	0.370	8.89	9.40	
D1	0.315	0.324	8.01	8.23	2
E	0.395	0.405	10.04	10.28	
E1	0.310	0.318	7.88	8.08	2
e	0.200 BSC.		5.08 BSC.		
L	0.580	0.620	14.73	15.75	
L1	0.090	0.110	2.29	2.79	4
L2	0.045	0.055	1.15	1.39	
L3	0.050	0.070	1.27	1.77	3
θ	0°	8°	0°	8°	

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